

SANYO Semiconductors DATA SHEET

SS1003M3 Schottky Barrier Diode 30V, 1.0A Rectifier

Applications

· High frequency rectification (switching regulators, converters, choppers).

Features

- · Low switching noise.
- Low forward voltage (I_F=1.0A, V_F max=0.43V).
- · Ultrasmall package permitting applied sets to be small and slim.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Repetitive Peak Reverse Voltage	VRRM		30	V
Nonrepetitive Peak Reverse Surge Voltage	VRSM		30	V
Average Output Current	IO		1.0	Α
Surge Forward Current	IFSM	50Hz sine wave, 1 cycle	10	Α
Junction Temperature	Tj		-55 to +125	°C
Storage Temperature	Tstg		-55 to +125	ç

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Offic
Reverse Voltage	VR	I _R =0.5mA	30			V
Forward Voltage	VF1	IF=0.5A		0.32	0.37	V
	V _F 2	IF=1.0A		0.38	0.43	V
Reverse Current	IR	V _R =16V			360	μΑ
Interterminal Capacitance	С	V _R =10V, f=1MHz		27		pF
Reverse Recovery Time	t _{rr}	I _F =I _R =100mA, See specified Test Circuit.			10	ns

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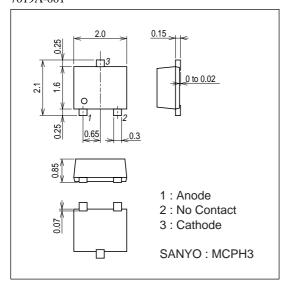
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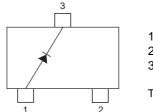
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	- Offic
Thermal Resistance	Rth(j-a)1	Mounted in Cu-foiled area of 0.72mm ² ×0.03mm		94.7		°C/W
		on glass epoxy board				
	Rth(j-a)2	Mounted on a ceramic board (500mm ² ×0.8mm)		67.7		°C/W

Package Dimensions

unit : mm (typ) 7019A-001



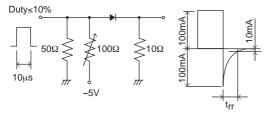
Electrical Connection

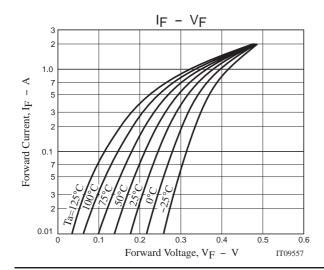


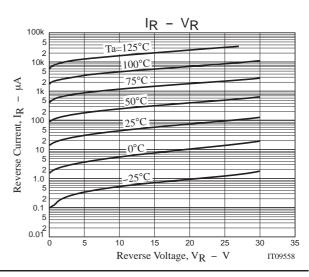
1 : Anode 2 : No Contact 3 : Cathode

Top view

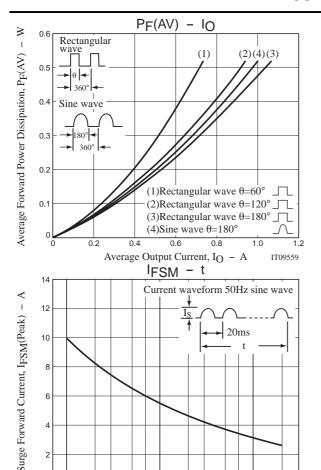
trr Test Circuit







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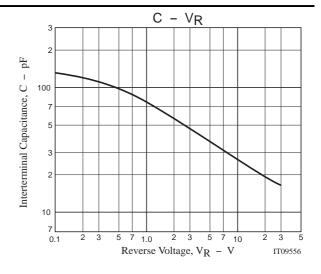
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